## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low current rectification and high speed
switching applications

## Features

- Extremely small surface mounting type

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings $\left(\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}\right)$

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 30 | V |
| Mean Rectifying Current | $\mathrm{I}_{\mathrm{O}}$ | 200 | mA |
| Peak Forward Surge Current (60Hz for Cyc.) | $\mathrm{I}_{\mathrm{FSM}}$ | 1 | A |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -40 to +125 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :---: | :---: | :---: | :---: |
| Forward Voltage <br> at $I_{F}=200 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | 0.5 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=10 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | 30 | $\mu \mathrm{~A}$ |



Fig. 1 Forward characteristics


Fig. 3 Capacitance between terminals characteristics


Fig. 2 Reverse characteristics


Fig. 4 Derating curve (mounting on glass epoxy PCBs)

## PACKAGE OUTLINE



| UNIT | A | $\mathrm{b}_{\mathrm{p}}$ | C | D | E | $\mathrm{H}_{\mathrm{E}}$ | V | $\angle$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | 0.70 | 0.4 | 0.135 | 1.25 | 0.85 | 1.7 | 0.1 | $5^{\circ}$ |
|  | 0.60 | 0.3 | 0.127 | 1.15 | 0.75 | 1.5 |  |  |

